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B. TECH.

SIXTH SEMESTER EXAMINATION, 2003-2004

MICROWAVE ENGINEERING

Time : 3 Hours

Total Marks : 100

Note : (1) Attempt ALL the questions.

(2) Assume suitable data, if necessary.

1. Attempt any FOUR parts of the following :—

- (a) What do subscripts m and n denote in rectangular and circular waveguides ? Why is TM_{01} mode not possible in rectangular waveguides whereas it does exist in circular waveguides ? (2.5×2)
- (b) When the dominant mode is propagated in an airfilled standard rectangular waveguide, the guide wavelength at a frequency of 9 GHz, is 4 cm. Calculate width of the guide. (5)
- (c) An airfilled rectangular waveguide of cross-section 1 cm × 2 cm is operating in TE_{10} mode at a frequency of 12 GHz. What is the maximum power handling capacity of the guide, if the dielectric strength of the medium is 3×10^6 V/m ? (5)
- (d) Discuss the attenuation characteristics of the circular waveguide. Why does TE_{10} mode show a very low loss at higher frequencies ? (3+2)
- (e) An airfilled circular waveguide having an inner radius of 1 cm, is excited in dominant mode at 10 GHz. Find :

- (i) the cut-off frequency of dominant mode,
 - (ii) guide wavelength,
 - (iii) wave impedance, and
 - (iv) bandwidth for operation in dominant mode only. (1.25×4)
- (f) Give the physical structure and field distribution of a microstrip line. Why can a pure TEM mode not be propagated in a microstrip line ? (2.5×2)

2. Attempt any FOUR parts of the following :—

- (a) Show that a rectangular cavity may be viewed as a rectangular waveguide shorted at both ends. Also find the resonance condition. (2.5×2)
- (b) Explain the construction and working of Bethe Hole coupler. Under what conditions does the coupler give maximum directivity ? (3+2)
- (c) What is Magic Tee ? Why is it called so ? Explain the characteristics of the tee considering various input/output conditions. (1+1+3)
- (d) What is Hybrid Ring ? Describe the physical structure and operation of a series-connected waveguide hybrid ring. Why is it called rate-race ? (1+1+3)
- (e) What are the disadvantages of a variable flap attenuator ? How are they overcome in rotary vane attenuator ? (1+4)
- (f) What is Circulator ? How can a four port circulator be realized using two magic tees and a gyrator ? (1+4)

3. Attempt any TWO parts of the following : —

(a) (i) How is slotted line used for measurement of impedance of an unknown load ? (5)

(ii) A 50Ω lossless line is terminated in an unknown impedance. The VSWR of the load is 2. When the load is replaced by a short, the minima shifts 1.5 cm towards the load and the successive voltage minima are 5 cm apart. What is the load impedance ? (5)

(b) What is Bolometer ? Give the construction of a thermistor mount and explain the method of microwave power measurement using dual bolometer bridge. What is the function of second bridge ? (2+2+4+2)

(c) (i) What is Wavemeter ? Differentiate between transmission and reaction type wavemeters. Which type is generally used in the microwave test bench in the laboratory ? Explain its construction and working. (2+2+1+3)

(ii) State how to measure the frequency of the source without using a wavemeter in the microwave test bench. (2)

4. Answer any TWO parts of the following :—

(a) Why is Magnetron also called 'Extended Interaction' tube ? Derive the expression for the Hull cut-off magnetic flux density in a cylindrical magnetron. (3+7)

(b) An identical two-cavity Klystron amplifier operates at 4 GHz with $V_0 = 1kV$,

$I_0 = 22 \text{ mA}$, cavity gap = 1 mm, drift space = 3 cm and cathode cavity total effective shunt conductance $G_{sh} = 0.3 \times 10^{-4}$ mhos. Calculate :

- (i) Beam coupling coefficient and the input cavity voltage magnitude for maximum output voltage. (5)
- (ii) Voltage gain and efficiency, neglecting beam loading. (5)
2. (c) How is continuous interaction between the electron beam and RF field ensured in a TWT ? Using suitable diagrams, show that the favourable interactions are far more than the unfavourable interactions, resulting in amplification. (4+6)
5. Answer any FOUR parts of the following :—
- (a) How can PIN diode be used as a microwave switch ? Describe a single PIN switch in shunt and series mounting configurations. (2.5×2)
- (b) How is plasma trapped in a TRAPATT diode ? Why is the operating frequency of this diode lower than IMPATT ? Give its major merits and demerits. (2+2+1)
- (c) Discuss the formation and growth of the high field domain in a TED. (5)
- (d) What are the conditions to be satisfied by the semiconductor in order to exhibit transferred electron effect ? What are the limitations of Ga As diode ? (3+2)



(e) Discuss the differences between tunnel diode and ordinary PN junction diode. Show that an amplifier with infinite gain can be built by connecting the tunnel diode to a circulator. (2.5×2)

(f) What does acronym IMPATT stand for ? Why does the device show a differential negative resistance ? Give the physical structure, doping profile and electric field distribution of a double drift region IMPATT diode. What is the advantage of double drift region over single drift region ? (1+1+2+1) 100



3×2)

(5)

(5)

3+2)